



STB230NH03L

N-channel 30V - 80A - D²PAK
STripFET™ Power MOSFET

Features

Type	V _{DSS}	R _{DS(on)}	I _D
STB230NH03L	30V	< 3mΩ	80A ⁽¹⁾

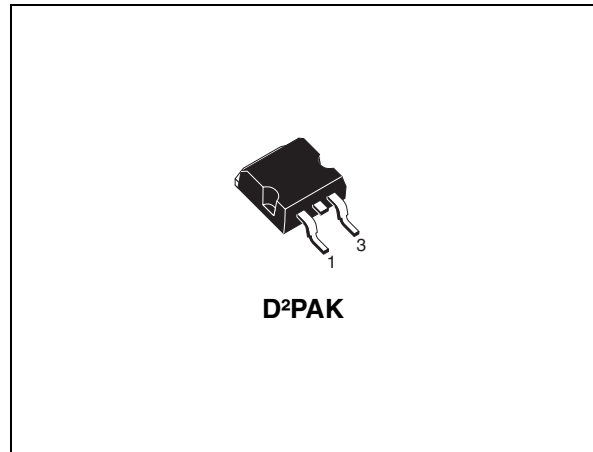
1. This value is limited by package
- R_{DS(on)} Qg industry's benchmark
 - Conduction losses reduced
 - Switching losses reduced
 - Low threshold device

Description

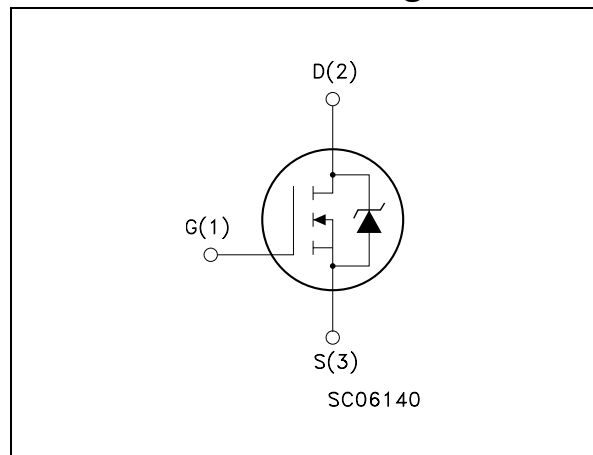
This product utilizes the latest advanced design rules of ST's proprietary STripFET™ technology. This is suitable for the most demanding DC-DC converter application where high efficiency is to be achieved.

Applications

- Switching applications
 - Specifically designed and optimized for high efficiency DC/DC converters
 - OR-ing



Internal schematic diagram



Order code

Part number	Marking	Package	Packaging
STB230NH03L	B230NH03L	D ² PAK	Tape & reel

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1 Electrical ratings

Table 1. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage ($V_{GS} = 0$)	30	V
V_{GS}	Gate-source voltage	± 20	V
$I_D^{(1)}$	Drain current (continuous) at $T_C = 25^\circ\text{C}$	250	A
$I_D^{(1)}$	Drain current (continuous) at $T_C = 100^\circ\text{C}$	178	A
$I_D^{(2)}$	Drain current (continuous) at $T_C = 25^\circ\text{C}$	80	A
$I_{DM}^{(3)}$	Drain current (pulsed)	1000	A
$P_{TOT}^{(4)}$	Total dissipation at $T_C = 25^\circ\text{C}$	300	W
	Derating factor	2	W/ $^\circ\text{C}$
T_J	Operating junction temperature	-55 to 175	$^\circ\text{C}$

1. This value is silicon limited
2. This value is limited by package
3. Pulse width limited by safe operating area
4. This value is rated according to Rthj-c

Table 2. Thermal data

Symbol	Parameter	Value	Unit
R_{thJC}	Thermal resistance junction-case max	0.5	$^\circ\text{C}/\text{W}$
R_{thJA}	Thermal resistance junction-ambient max	62.5	$^\circ\text{C}/\text{W}$
T_I	Maximum lead temperature for soldering purpose	300	$^\circ\text{C}$

Table 3. Avalanche data

Symbol	Parameter	Value	Unit
I_{AS}	Avalanche current	60	A
$E_{AS}^{(1)}$	Single pulse avalanche energy	1150	mJ

1. Starting $T_j = 25^\circ\text{C}$, $I_D = I_{AV}$, $V_{DD} = 24\text{V}$

2 Electrical characteristics

($T_{CASE}=25^{\circ}C$ unless otherwise specified)

Table 4. On/off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$I_D = 1mA, V_{GS} = 0$	30			V
I_{DSS}	Zero gate voltage drain current ($V_{GS} = 0$)	$V_{DS} = 30V,$ $V_{DS} = 30V, T_c = 125^{\circ}C$			1 10	μA μA
I_{GSS}	Gate body leakage current ($V_{DS} = 0$)	$V_{GS} = \pm 20V$			± 100	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}, I_D = 250\mu A$	1	1.5	2.5	V
$R_{DS(on)}$	Static drain-source on resistance	$V_{GS} = 10V, I_D = 40A$		2.3	3	$m\Omega$

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	$V_{DS} = 10V, f = 1 MHz, V_{GS} = 0$		4700		pF
C_{oss}	Output capacitance			1600		pF
C_{rss}	Reverse transfer capacitance			85		pF
Q_g	Total gate charge	$V_{DD} = 15V, I_D = 60A$		72		nC
Q_{gs}	Gate-source charge	$V_{GS} = 10V$		15		nC
Q_{gd}	Gate-drain charge	(see Figure 13)		11		nC
R_G	Gate input resistance	$f = 1 MHz$ Gate DC Bias = 0 Test signal level = 20mV open drain		5.5		Ω

Table 6. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ t_r	Turn-on delay time Rise time	$V_{DD}=15V$, $I_D=60A$, $R_G=4.7\Omega$, $V_{GS}=10V$ (see Figure 12)		11 322		ns ns
$t_{d(off)}$ t_f	Turn-off delay time Fall time	$V_{DD}=15V$, $I_D=60A$, $R_G=4.7\Omega$, $V_{GS}=10V$ (see Figure 12)		123 102		ns ns

Table 7. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$I_{SD}^{(1)}$ $I_{SDM}^{(2)}$	Source-drain current Source-drain current (pulsed)				250 1000	A A
$V_{SD}^{(3)}$	Forward on voltage	$I_{SD}=40A$, $V_{GS}=0$			1.3	V
t_{rr} Q_{rr} I_{RRM}	Reverse recovery time Reverse recovery charge Reverse recovery current	$I_{SD}=120A$, $di/dt = 100A/\mu s$, $V_{DD}=20V$, $T_j=25^\circ C$ (see Figure 17)		42 34.7 1.6		ns nC A
t_{rr} Q_{rr} I_{RRM}	Reverse recovery time Reverse recovery charge Reverse recovery current	$I_{SD}=120A$, $di/dt = 100A/\mu s$, $V_{DD}=20V$, $T_j=150^\circ C$ (see Figure 17)		47 41.3 1.8		ns nC A

1. This value is silicon limited
2. Pulse width limited by safe operating area
3. Pulsed: pulse duration=300 μs , duty cycle 1.5%

2.1 Electrical characteristics (curves)

Figure 1. Safe operating area

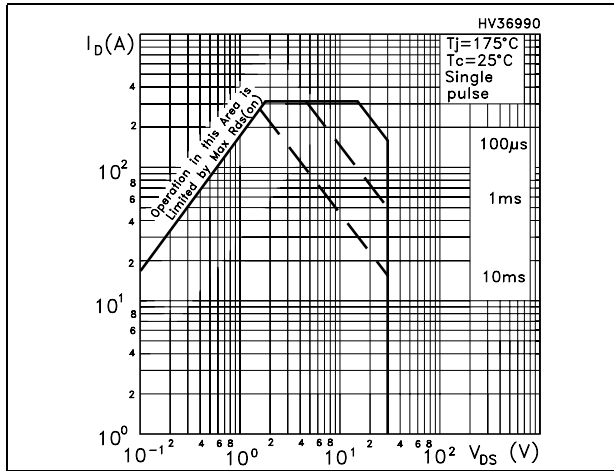


Figure 2. Thermal impedance

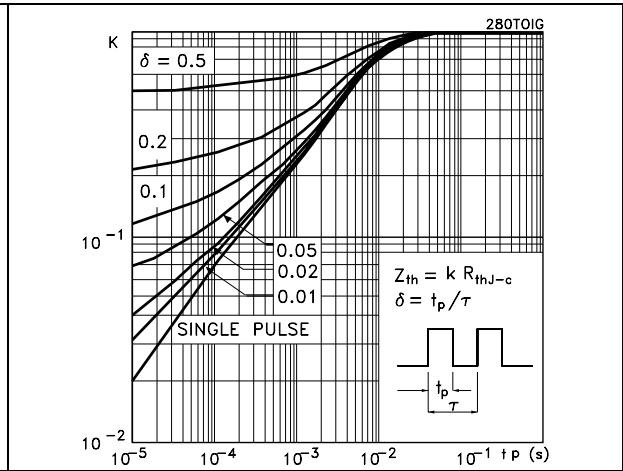


Figure 3. Output characteristics

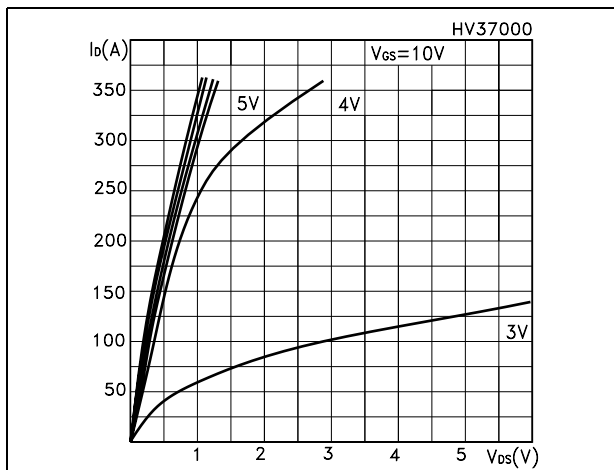


Figure 4. Transfer characteristics

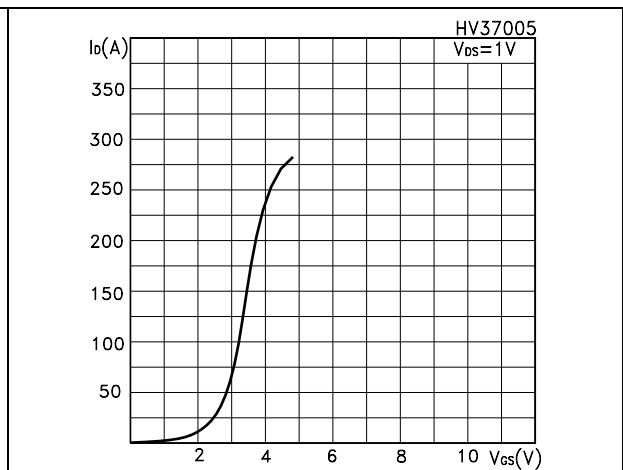


Figure 5. Static drain-source on resistance

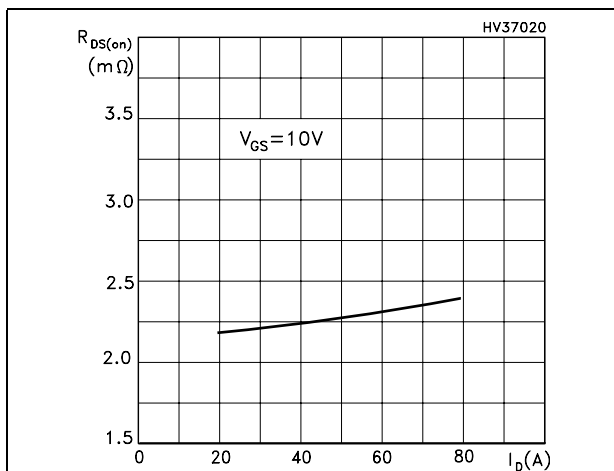


Figure 6. Normalized BV_{DSS} vs temperature

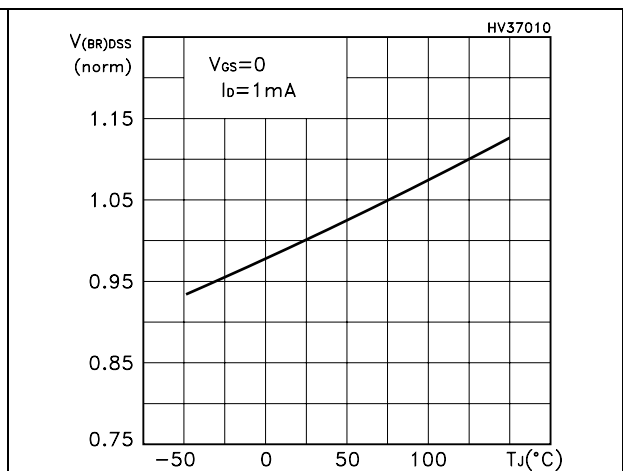


Figure 7. Gate charge vs gate-source voltage Figure 8. Capacitance variations

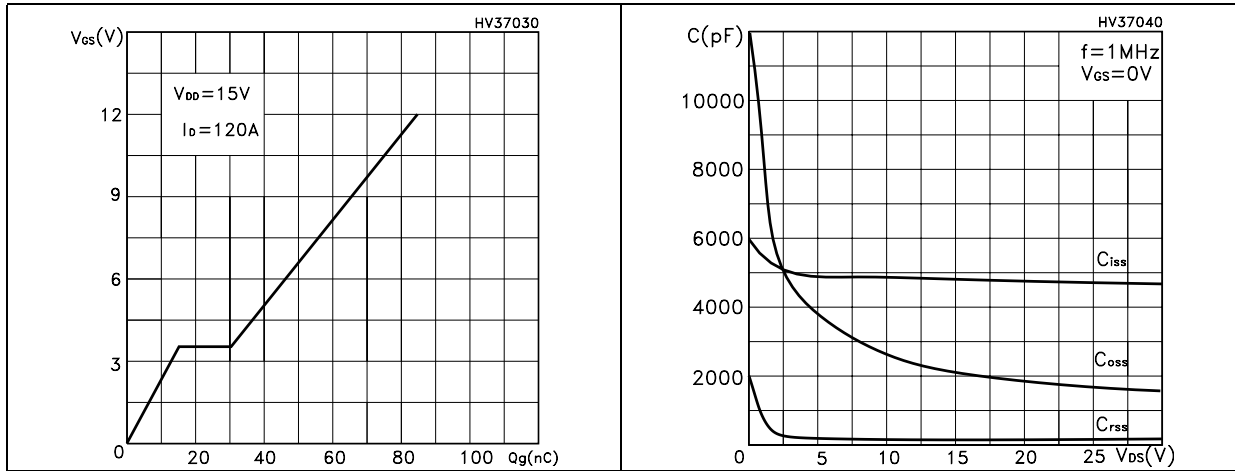


Figure 9. Normalized gate threshold voltage vs temperature Figure 10. Normalized on resistance vs temperature

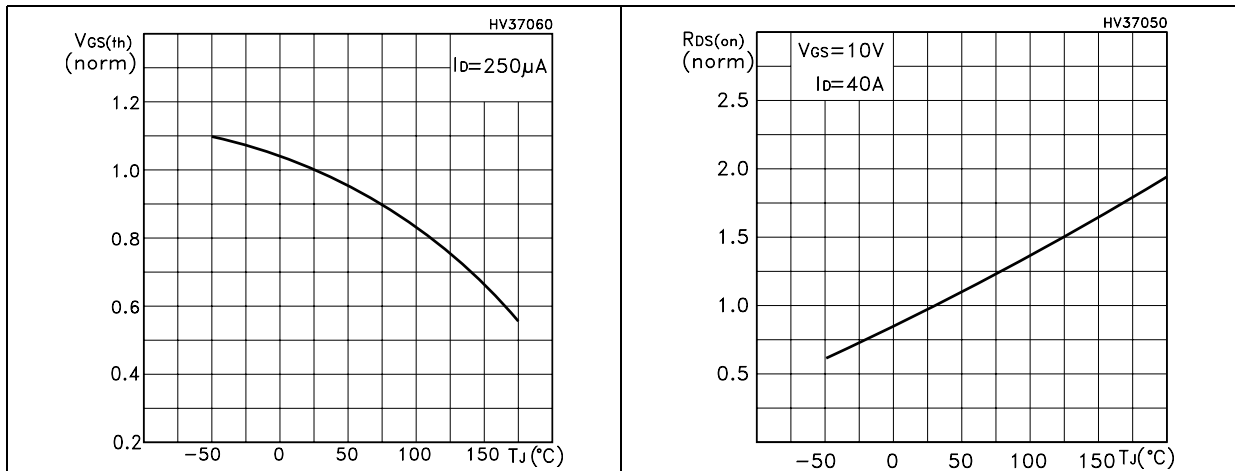
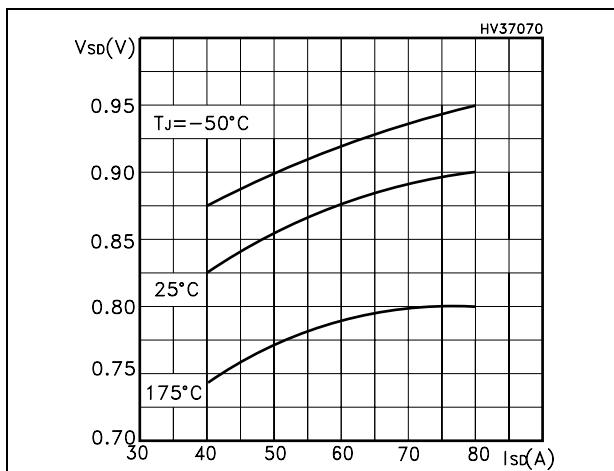


Figure 11. Source-drain diode forward characteristics



3 Test circuit

Figure 12. Switching times test circuit for resistive load

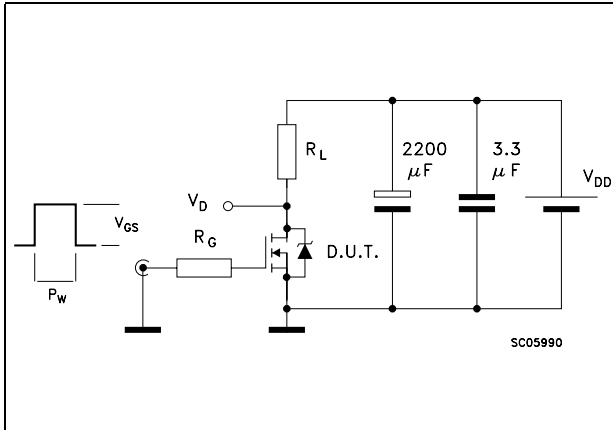


Figure 13. Gate charge test circuit

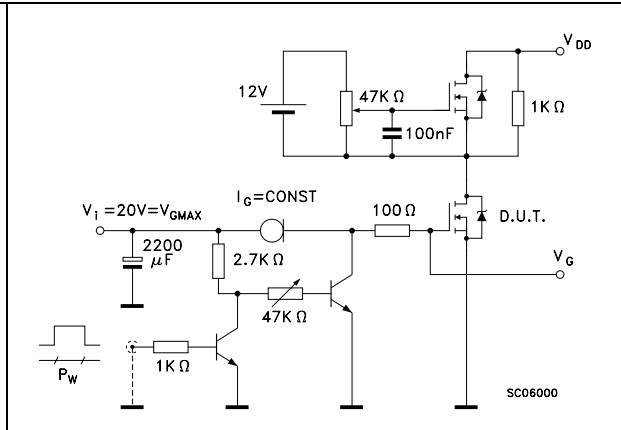


Figure 14. Test circuit for inductive load switching and diode recovery times

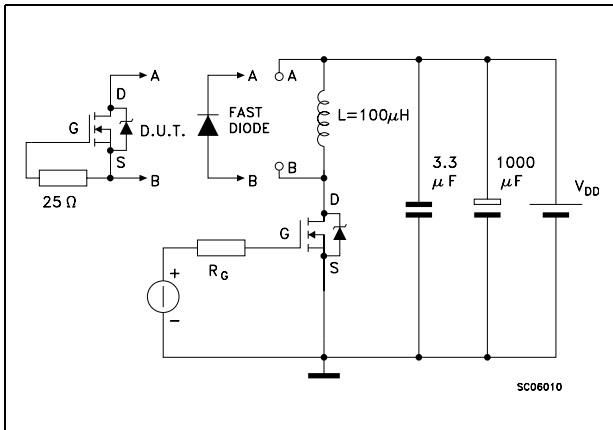


Figure 15. Unclamped Inductive load test circuit

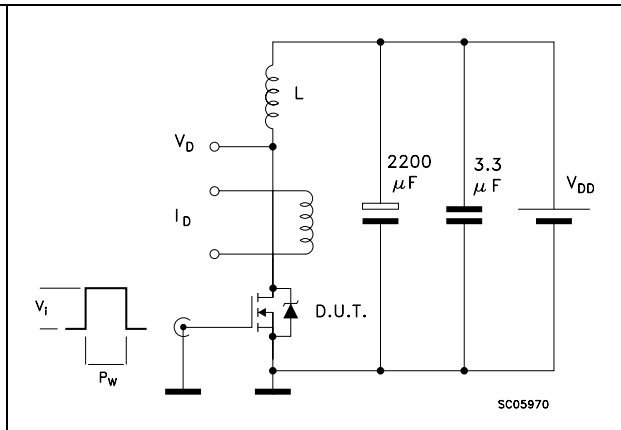


Figure 16. Unclamped inductive waveform

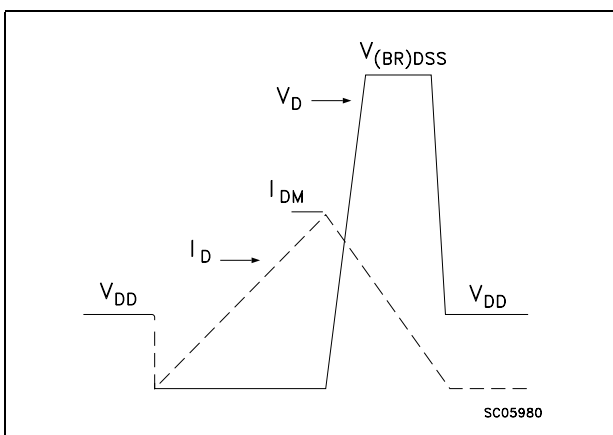
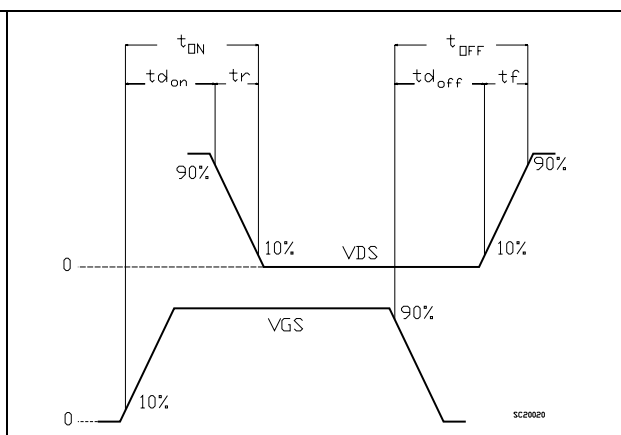


Figure 17. Switching time waveform

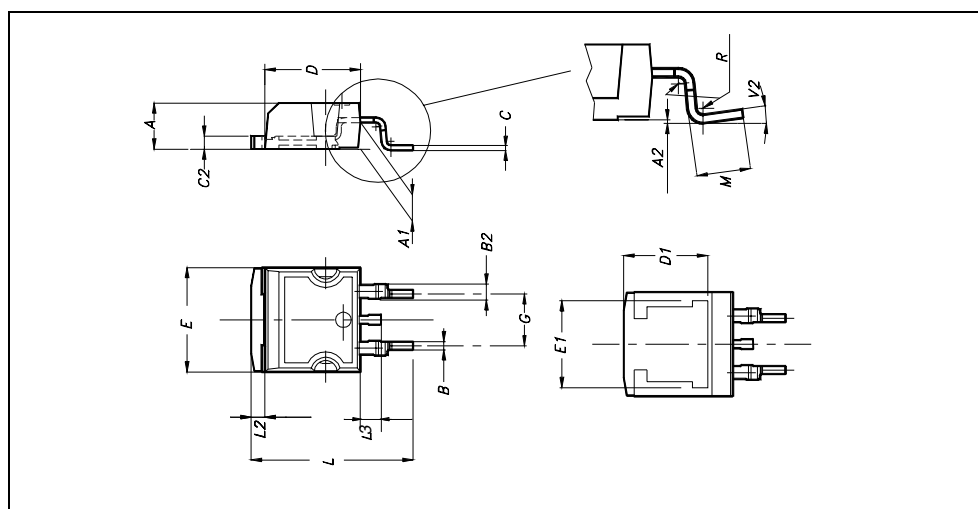


4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com

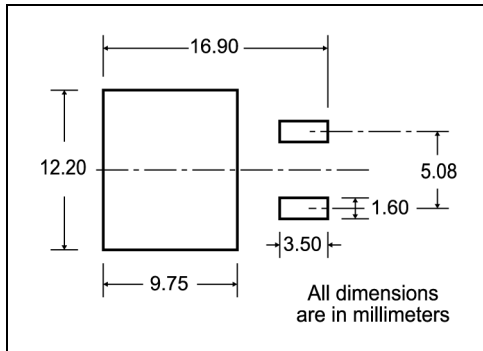
D²PAK MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A	4.4		4.6	0.173		0.181
A1	2.49		2.69	0.098		0.106
A2	0.03		0.23	0.001		0.009
B	0.7		0.93	0.027		0.036
B2	1.14		1.7	0.044		0.067
C	0.45		0.6	0.017		0.023
C2	1.23		1.36	0.048		0.053
D	8.95		9.35	0.352		0.368
D1		8			0.315	
E	10		10.4	0.393		
E1		8.5			0.334	
G	4.88		5.28	0.192		0.208
L	15		15.85	0.590		0.625
L2	1.27		1.4	0.050		0.055
L3	1.4		1.75	0.055		0.068
M	2.4		3.2	0.094		0.126
R		0.4			0.015	
V2	0°		4°			



5 Packaging mechanical data

D²PAK FOOTPRINT



TAPE AND REEL SHIPMENT

40 mm min. Access hole at slot location

Full radius

Tape slot in core for tape start 2.5mm min. width

G measured at hub

REEL MECHANICAL DATA

DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A		330		12.992
B	1.5		0.059	
C	12.8	13.2	0.504	0.520
D	20.2		0.795	
G	24.4	26.4	0.960	1.039
N	100		3.937	
T		30.4		1.197

BASE QTY	BULK QTY
1000	1000

TAPE MECHANICAL DATA

DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A0	10.5	10.7	0.413	0.421
B0	15.7	15.9	0.618	0.626
D	1.5	1.6	0.059	0.063
D1	1.59	1.61	0.062	0.063
E	1.65	1.85	0.065	0.073
F	11.4	11.6	0.449	0.456
K0	4.8	5.0	0.189	0.197
P0	3.9	4.1	0.153	0.161
P1	11.9	12.1	0.468	0.476
P2	1.9	2.1	0.075	0.082
R	50		1.574	
T	0.25	0.35	0.0098	0.0137
W	23.7	24.3	0.933	0.956

10 pitches cumulative tolerance on tape +/- 0.2 mm

Center line of cavity

User Direction of Feed

TRL

FEED DIRECTION

Bending radius R min.

* on sales type

6 Revision history

Table 8. Revision history

Date	Revision	Changes
08-Jun-2007	1	Initial release.

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